

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-80V	15mΩ@-10V	-100A
	20mΩ@-4.5V	

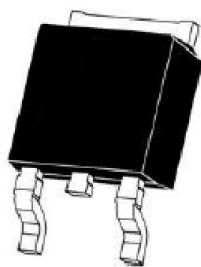
Feature

- Advanced trench technology
- Excellent $R_{DS(on)}$
- Low Gate Charge

Application

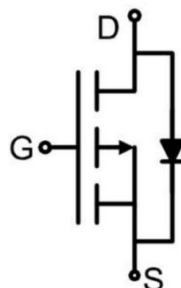
- Lithium battery protection
- Wireless impact
- Mobile phone fast charging

Package

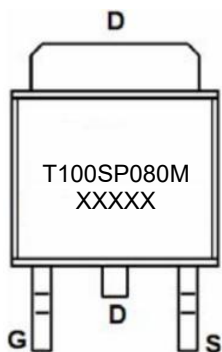


TO-252AB

Circuit diagram



Marking



Absolute maximum ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-80	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current ¹⁾ (V _{GS} = -10V)	I _D	-100	A
Continuous Drain Current ¹⁾ (V _{GS} = -10V, T _c = 100°C)	I _D (100°C)	-65	A
Pulsed Drain Current ²⁾	I _{DM}	-300	A
Single Pulse Avalanche Energy ³⁾	E _{AS}	650	mJ
Power Dissipation ⁴⁾	P _D	142	W
Thermal Resistance Junction to Case ¹⁾	R _{θJC}	0.88	°C/W
Operating Junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Electrical characteristics (T_c=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-80			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-64V, V _{GS} =0V, T _J =25℃			-1	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.2	-2	-2.5	V
Drain-source on-resistance ²⁾	R _{DS(on)}	V _{GS} =-10V, I _D =-20A		12	15	mΩ
		V _{GS} =-4.5V, I _D =-15A		15	20	
Dynamic characteristics ⁵⁾						
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, f =1MHz		12071		pF
Output Capacitance	C _{oss}			966		
Reverse Transfer Capacitance	C _{rss}			858		
Total Gate Charge	Q _g	V _{DS} =-40V, V _{GS} =-10V I _D =-20A		168		nC
Gate-Source Charge	Q _{gs}			47		
Gate-Drain Charge	Q _{gd}			78		
Turn-on delay time	t _{d(on)}	V _{DS} =-40V, V _{GS} =-10V I _D =-20A, R _L =2Ω, R _G =6Ω		70		nS
Turn-on rise time	t _r			205		
Turn-off delay time	t _{d(off)}			402		
Turn-off fall time	t _f			402		
Source-Drain Diode characteristics						
Diode Forward Current	I _s				-100	A
Diode Forward voltage	V _{SD}	V _{GS} =0V, I _s =-1A, T _J =25℃			-1.2	V

Notes:

- 1) The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2) The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
- 3) The EAS data shows Max. rating. The test condition is V_{DS} = -64V, V_{GS} = -10V, L = 0.1mH, I_{AS} = -80A.
- 4) The power dissipation is limited by 150°C junction temperature.
- 5) Guaranteed by design, not subject to production testing.

Typical Characteristics

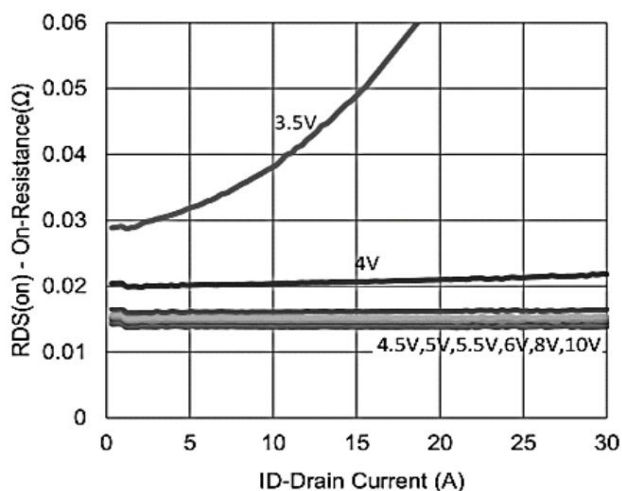


Fig.1 On-Resistance vs. Drain Current

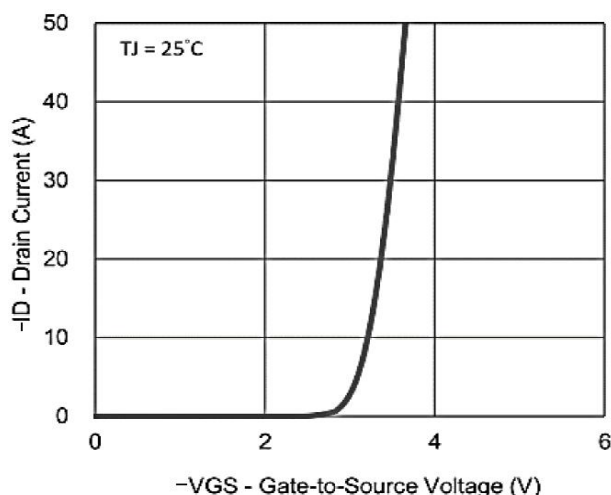


Fig.2 Transfer Characteristics

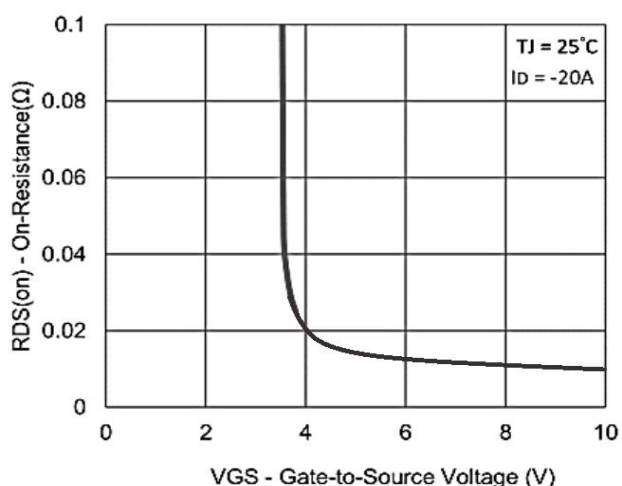


Fig.3 On-Resistance vs. Gate-to-Source Voltage

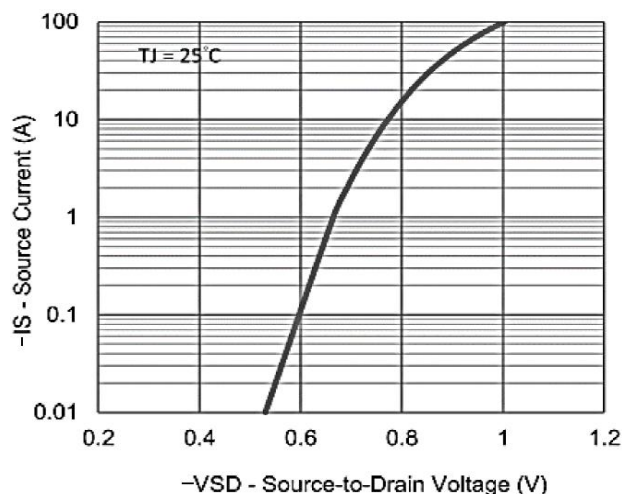


Fig.4 Drain-to-Source Forward Voltage

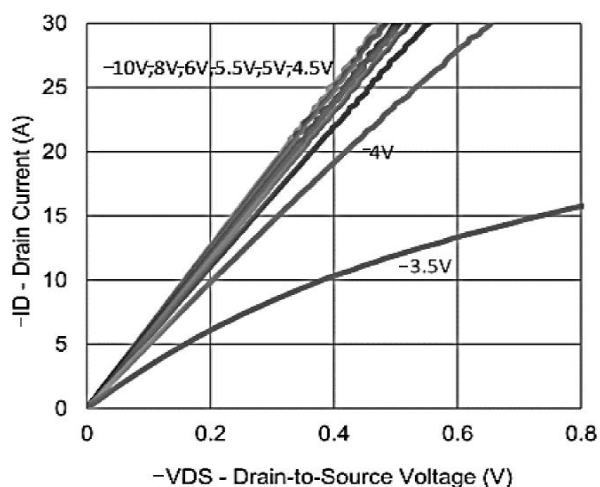


Fig.5 Output Characteristics

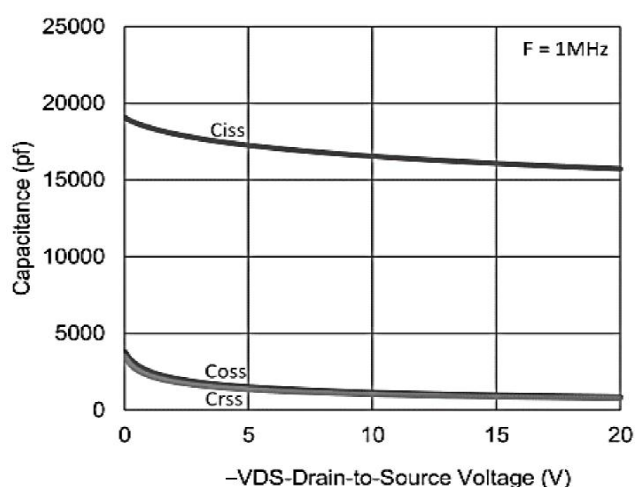
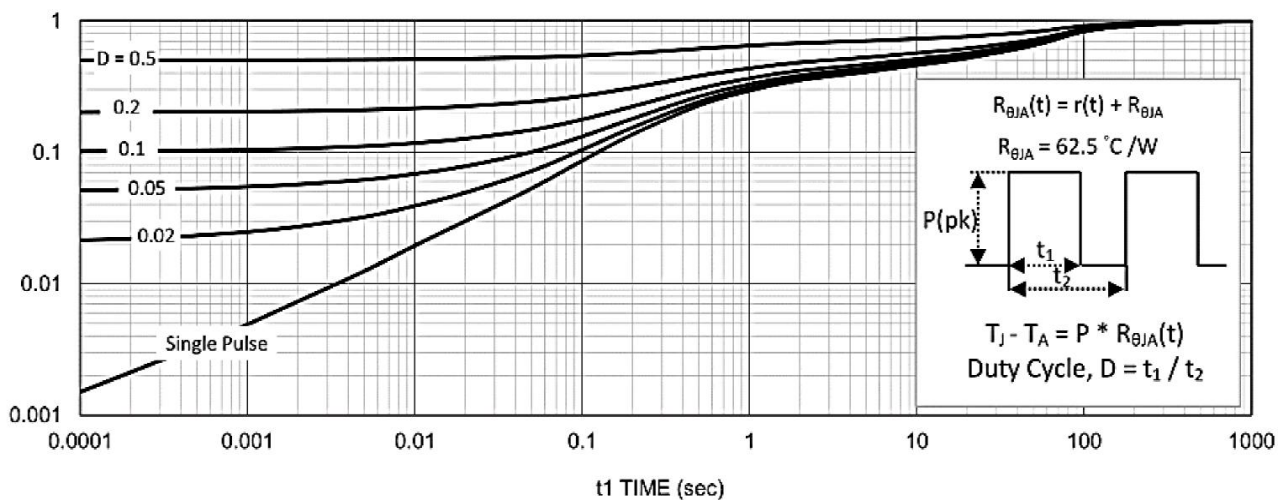
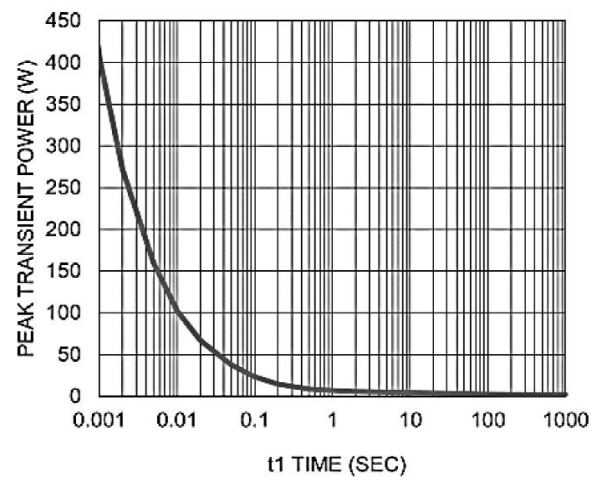
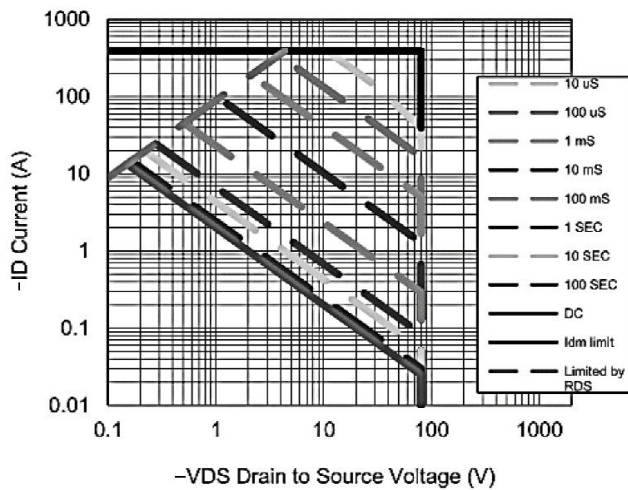
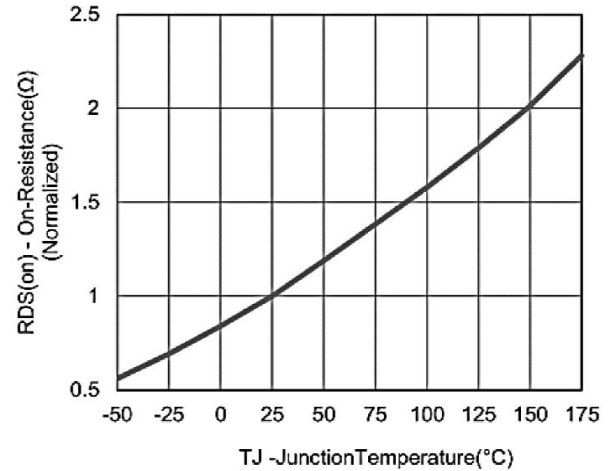
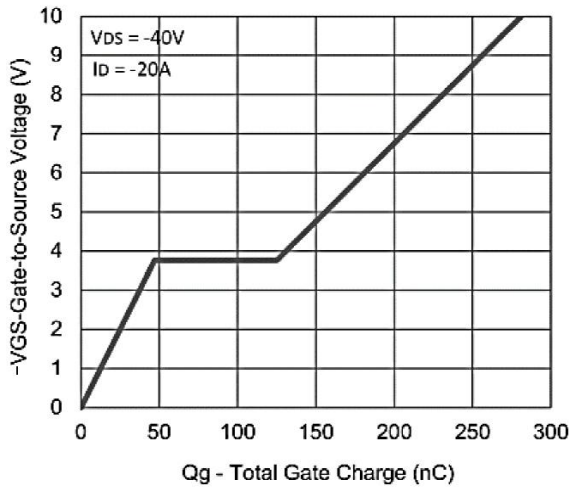
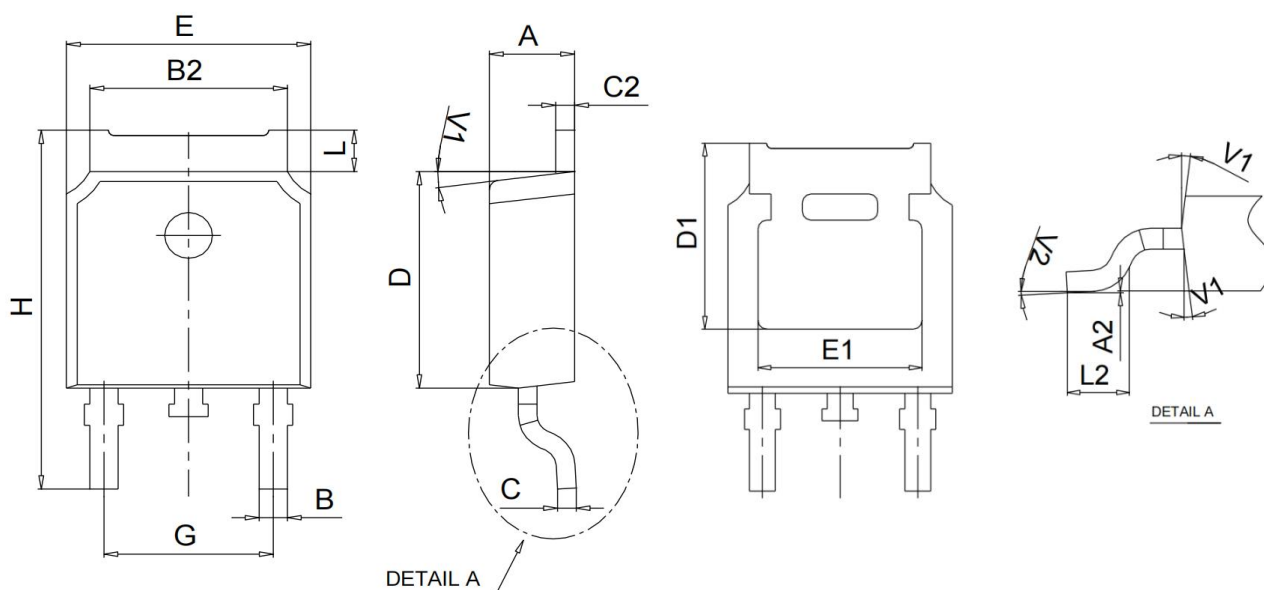


Fig.6 Capacitance

Typical Characteristics



TO-252AB Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.100	2.500	0.083	0.098
A2	0.000	0.100	0.000	0.004
B	0.660	0.860	0.026	0.034
B2	5.180	5.480	0.202	0.216
C	0.400	0.600	0.016	0.024
C2	0.440	0.580	0.017	0.023
D	5.900	6.300	0.232	0.248
D1	5.300 REF.		0.209 REF.	
E	6.400	6.800	0.252	0.268
E1	4.630	-	0.182	-
G	4.470	4.670	0.176	0.184
H	9.500	10.700	0.374	0.421
L	1.090	1.210	0.043	0.048
L2	1.350	1.650	0.053	0.065
V1	7° BSC.		7° BSC.	
V2	0°	6°	0°	6°